

### 1. General description

Planar passivated very sensitive gate four quadrant triac in a SOT54 (TO-92) plastic package intended for use in applications requiring enhanced noise immunity and direct interfacing to logic ICs and low power gate drivers.

### 2. Features and benefits

- Direct interfacing to logic level ICs
- Enhanced current surge capability
- · Enhanced noise immunity
- High blocking voltage capability
- · Planar passivated for voltage ruggedness and reliability
- Triggering in all four quadrants
- · Very sensitive gate in four quadrants

#### 3. Applications

- General purpose low power motor control
- Home appliances
- Industrial process control
- Low power AC Fan controllers

#### 4. Quick reference data

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
V <sub>DRM</sub>	repetitive peak off- state voltage		-	-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; T <sub>lead</sub> ≤ 45 °C; <u>Fig. 1;</u> <u>Fig. 2; Fig. 3</u>	-	-	1	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; $T_{j(init)} = 25 \text{ °C};$ $t_p = 20 \text{ ms}; \frac{\text{Fig. 4}}{25}; \frac{1}{25}$	-	-	12.5	A
		full sine wave; $T_{j(init)}$ = 25 °C; t <sub>p</sub> = 16.7 ms	-	-	13.8	A
Tj	junction temperature		-	-	125	°C
Static chara	octeristics					
I <sub>GT</sub>		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	3	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>i</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	3	mA

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Symbol	Parameter	Conditions	Min	Тур	Max	Unit
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	3	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	5	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	7	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
Dynamic chara	acteristics					
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; T <sub>j</sub> = 110 °C; (V <sub>DM</sub> = 67% of V <sub>DRM</sub> ); exponential waveform; gate open circuit; Fig. 12	80	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D$ = 400 V; T <sub>j</sub> = 110 °C; dI <sub>com</sub> / dt = 0.44 A/ms; gate open circuit	0.5	-	-	V/µs

## 5. Pinning information

Table 2. Pinning information							
Pin	Symbol	Description	Simplified outline	Graphic symbol			
1	T2	main terminal 2		T2T1			
2	G	gate	Цпп	Sym051			
3	Τ1	main terminal 1	TO-92 (SOT54)				

### 6. Ordering information

Table 3. Ordering information							
Type number	Package						
	Name	Description	Version				
Z0103NA0	TO-92	plastic single-ended leaded (through hole) package; 3 leads	SOT54				



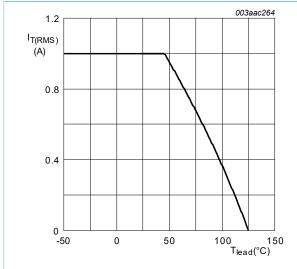
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### 7. Limiting values

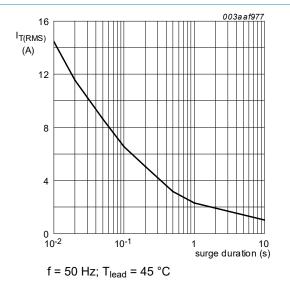
#### Table 4. Limiting values

In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V <sub>DRM</sub>	repetitive peak off-state voltage		-	800	V
I <sub>T(RMS)</sub>	RMS on-state current	full sine wave; $T_{lead} \le 45 \text{ °C}$ ; Fig. 1; Fig. 2; Fig. 3	-	1	A
I <sub>TSM</sub>	non-repetitive peak on- state current	full sine wave; T <sub>j(init)</sub> = 25 °C; t <sub>p</sub> = 20 ms; <u>Fig. 4; Fig. 5</u>	-	12.5	A
		full sine wave; $T_{j(init)}$ = 25 °C; $t_p$ = 16.7 ms	-	13.8	А
l <sup>2</sup> t	I <sup>2</sup> t for fusing	t <sub>p</sub> = 10 ms; SIN	-	0.78	A²s
dl <sub>T</sub> /dt	rate of rise of on-state current	I <sub>G</sub> = 20 mA; T2+ G+	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2+ G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G-	-	50	A/µs
		I <sub>G</sub> = 20 mA; T2- G+	-	20	A/µs
I <sub>GM</sub>	peak gate current		-	1	А
P <sub>GM</sub>	peak gate power		-	2	W
P <sub>G(AV)</sub>	average gate power	over any 20 ms period	-	0.1	W
T <sub>stg</sub>	storage temperature		-40	150	°C
Tj	junction temperature		-	125	°C



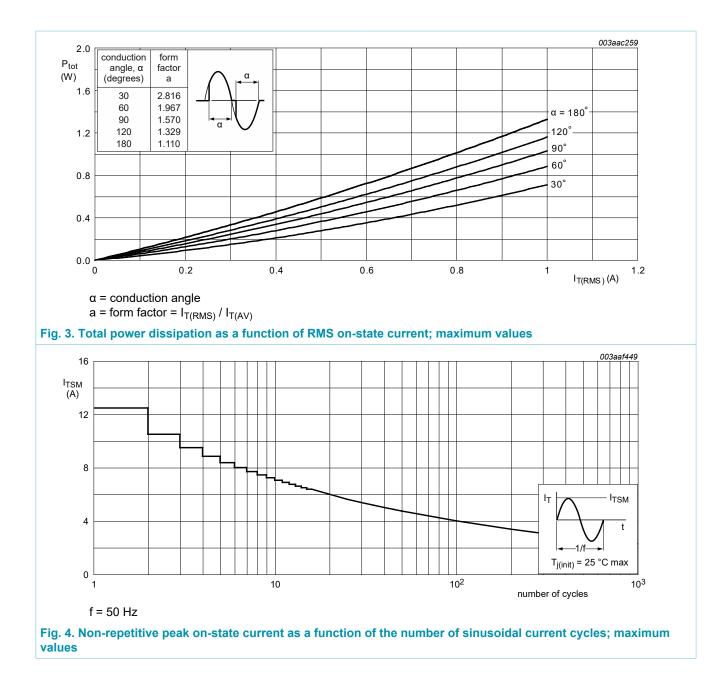






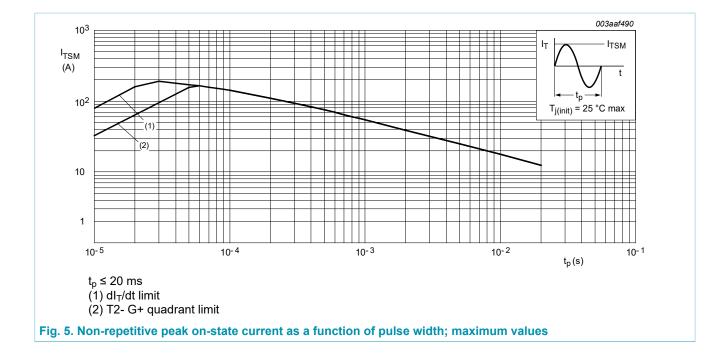
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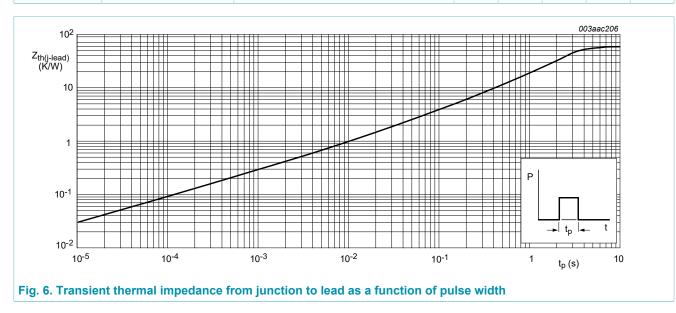


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#### 8. Thermal characteristics

Table 5. Therm	al characteristics					
Symbol	Parameter	Conditions	Min	Тур	Max	Unit
R <sub>th(j-lead)</sub>	thermal resistance from junction to lead	full cycle; <u>Fig. 6</u>	-	-	60	K/W
R <sub>th(j-a)</sub>	thermal resistance from junction to ambient free air	full cycle; printed circuit board mounted; lead length 4 mm	-	150	-	K/W



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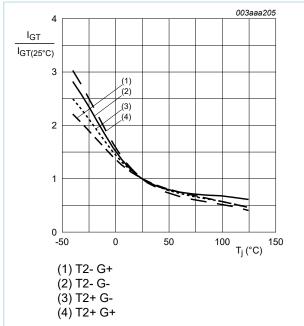
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### 9. Characteristics

Symbol	Parameter	Conditions	Min	Тур	Max	Unit
Static chara	octeristics		· · ·			
I <sub>GT</sub>	gate trigger current	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	3	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	3	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	3	mA
		V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 7</u>	0.2	-	5	mA
IL	latching current	V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	7	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2+ G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	20	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G-; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	7	mA
		V <sub>D</sub> = 12 V; I <sub>G</sub> = 0.1 A; T2- G+; T <sub>j</sub> = 25 °C; <u>Fig. 8</u>	-	-	7	mA
I <sub>H</sub>	holding current	V <sub>D</sub> = 12 V; T <sub>j</sub> = 25 °C; <u>Fig. 9</u>	-	-	7	mA
V <sub>T</sub>	on-state voltage	I <sub>T</sub> = 1 A; T <sub>j</sub> = 25 °C; <u>Fig. 10</u>	-	1.3	1.6	V
V <sub>GT</sub>	gate trigger voltage	V <sub>D</sub> = 12 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 25 °C; Fig. 11	-	-	1	V
		V <sub>D</sub> = 800 V; I <sub>T</sub> = 0.1 A; T <sub>j</sub> = 125 °C; Fig. 11	0.2	-	-	V
I <sub>D</sub>	off-state current	V <sub>D</sub> = 800 V; T <sub>j</sub> = 125 °C	-	-	0.5	mA
Dynamic ch	aracteristics	· · · · · · · · · · · · · · · · · · ·	·			
dV <sub>D</sub> /dt	rate of rise of off-state voltage	$V_{DM}$ = 536 V; $T_j$ = 110 °C; ( $V_{DM}$ = 67% of $V_{DRM}$ ); exponential waveform; gate open circuit; Fig. 12	80	-	-	V/µs
dV <sub>com</sub> /dt	rate of change of commutating voltage	$V_D = 400 \text{ V}; \text{ T}_j = 110 \text{ °C}; \text{ dI}_{com}/$ dt = 0.44 A/ms; gate open circuit	0.5	-	-	V/µs

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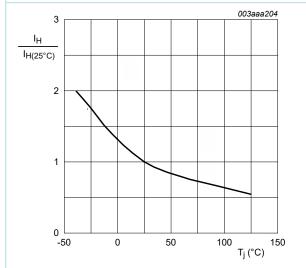
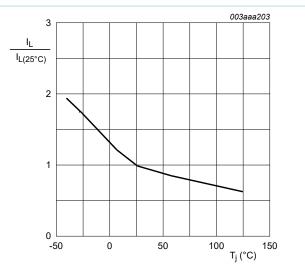
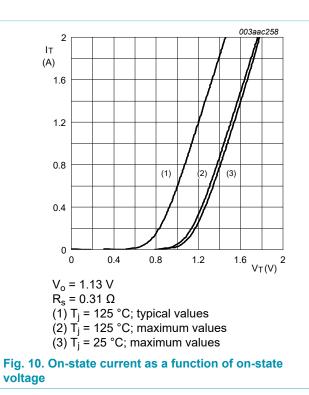


Fig. 9. Normalized holding current as a function of junction temperature

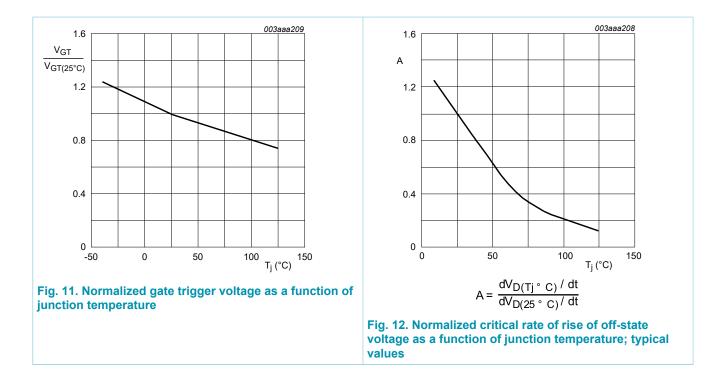






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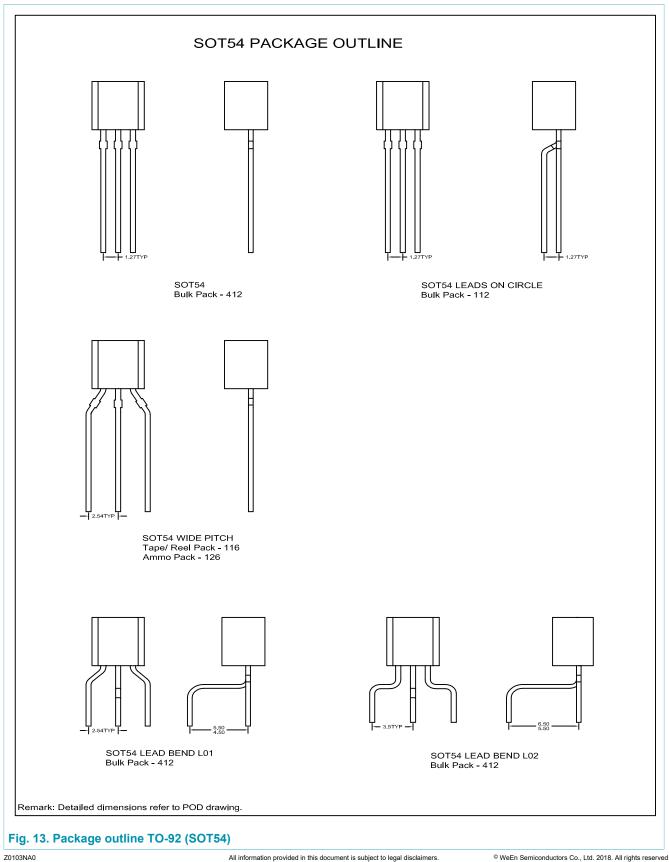
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### 10. Package outline



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#### **4Q Triac**

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